Abstracts

The Influence of I-Region Width Modulation on PIN Diode Attenuator Design

R.H. Caverly and Z.W. Tang. "The Influence of I-Region Width Modulation on PIN Diode Attenuator Design." 1995 MTT-S International Microwave Symposium Digest 95.1 (1995 Vol. I [MWSYM]): 87-90.

This paper discusses the effects of I-region width modulation on PIN diode attenuator performance. The work shows that the I-region thickness becomes thinner as the dc bias current decreases, and that over-estimates of PIN diode forward resistance can be the result.

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